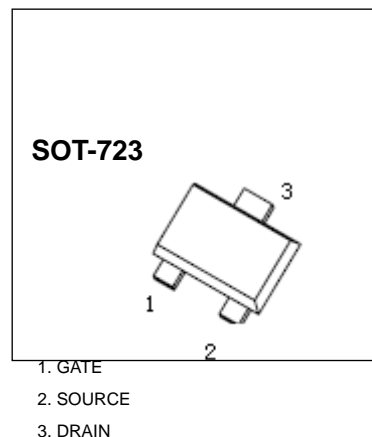


Plastic-Encapsulate MOSFETS

N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	380mΩ@4.5V	0.75A
	450mΩ@2.5V	
	800mΩ@1.8V	



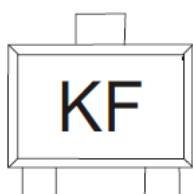
FEATURES

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

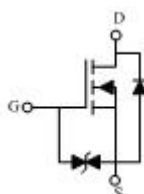
APPLICATION

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Typical Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current (note 1)	I_D	0.75	A
Pulsed Drain Current ($t_p=10 \mu s$)	I_{DM}	1.8	A
Power Dissipation (note 1)	P_D	150	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	833	$^{\circ}C/W$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^{\circ}C$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^{\circ}C$



MOSFET ELECTRICAL CHARACTERISTICS

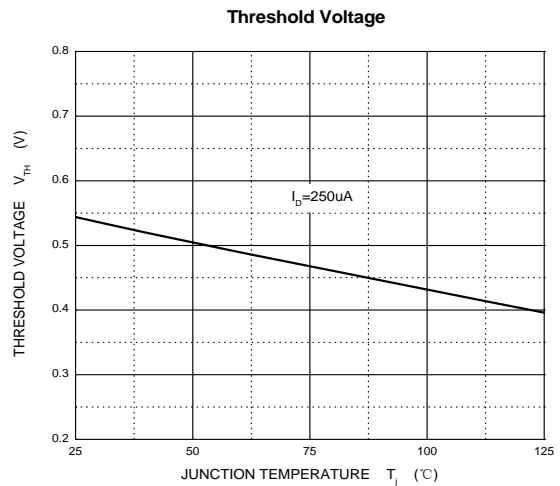
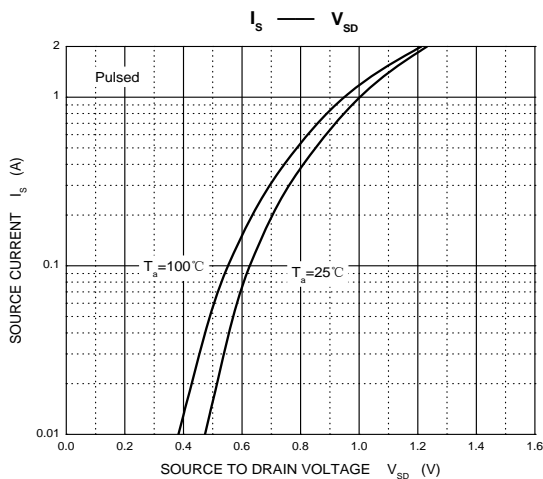
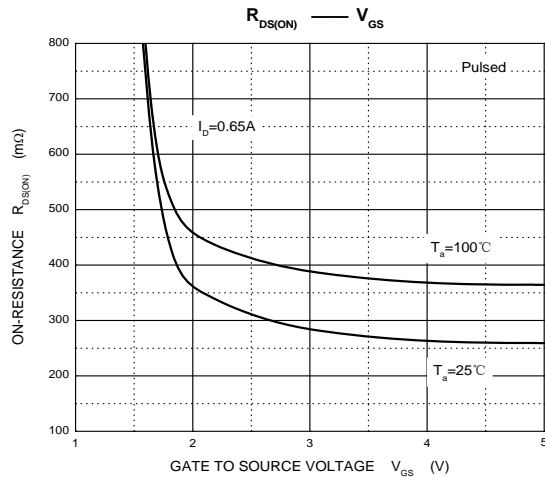
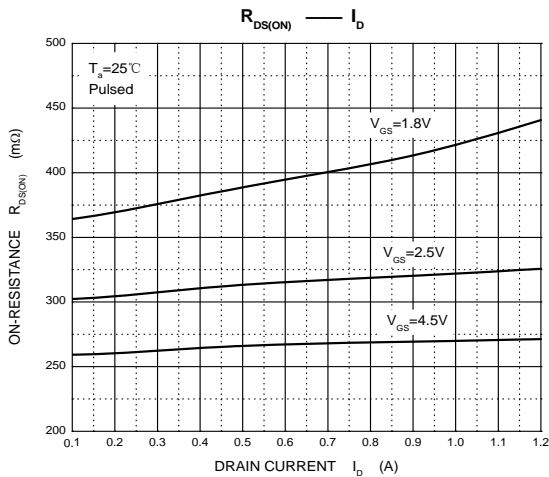
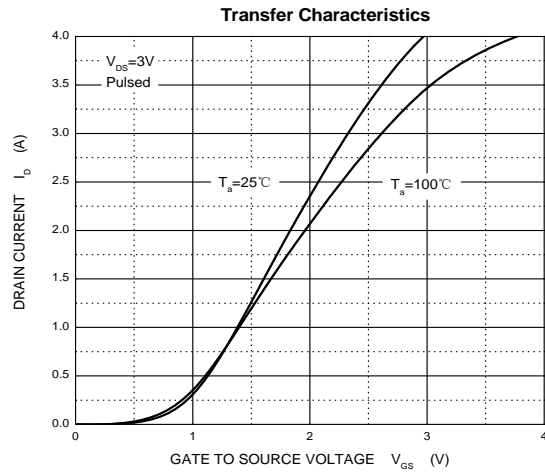
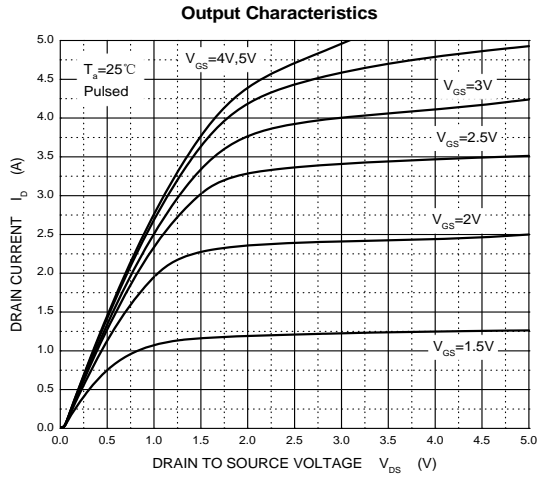
$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 20	μA
Gate threshold voltage (note 2)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.35	0.54	1.1	V
Drain-source on-resistance (note 2)	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 0.65A$		270	380	$m\Omega$
		$V_{GS} = 2.5V, I_D = 0.55A$		320	450	$m\Omega$
		$V_{GS} = 1.8V, I_D = 0.45A$		390	800	$m\Omega$
Forward transconductance (note 2)	g_{FS}	$V_{DS} = 10V, I_D = 0.8A$		1.6		S
Diode forward voltage	V_{SD}	$I_S = 0.15A, V_{GS} = 0V$			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$		79	120	pF
Output capacitance	C_{oss}			13	20	pF
Reverse transfer capacitance	C_{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time (note 3)	$t_{d(on)}$	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 500mA, R_{GEN} = 10\Omega$		6.7		ns
Turn-on rise time (note 3)	t_r			4.8		ns
Turn-off delay time (note 3)	$t_{d(off)}$			17.3		ns
Turn-off fall time (note 3)	t_f			7.4		ns
Total Gate Charge $Q_g [nC]$	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 0.65A$		11		nC
Gate-Source Charge $Q_{gs} [nC]$	Q_{gs}			11		nC
Gate-Drain Charge $Q_{gd} [nC]$	Q_{gd}			11		nC

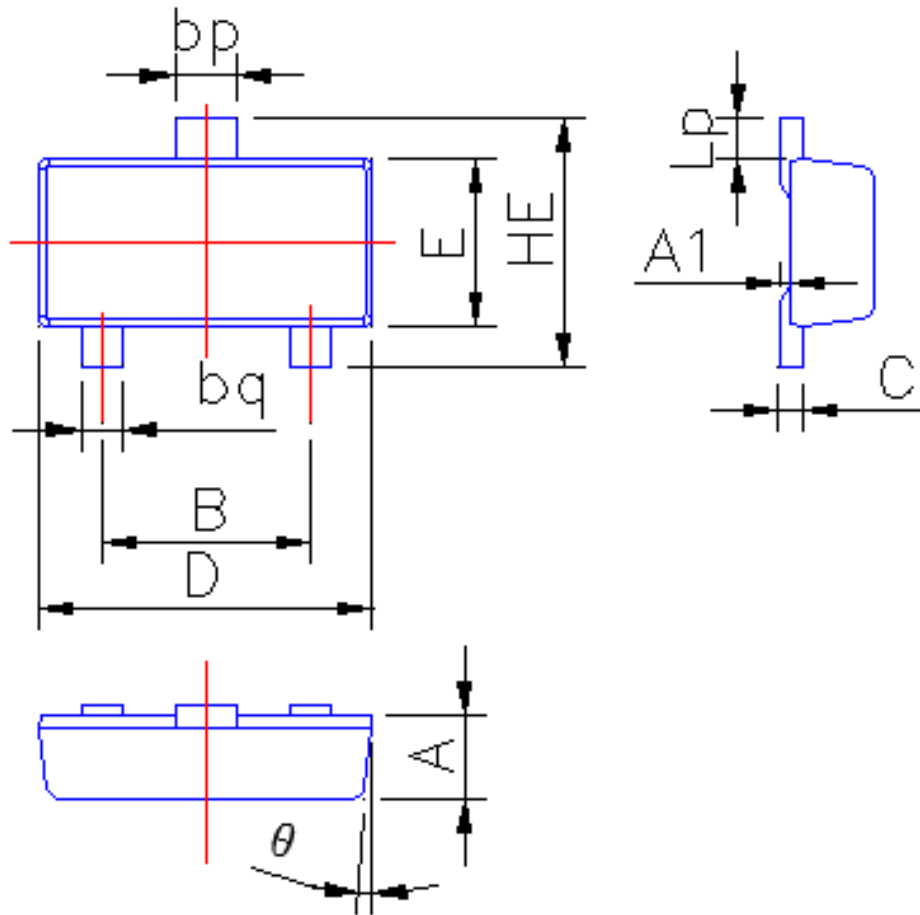
Notes :

- Surface mounted on FR4 board using the minimum recommended pad size.
- Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
- Switching characteristics are independent of operating junction temperatures.
- Guaranteed by design, not subject to producing.

Typical Characteristics



SOT-723-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.40	0.45
A1	0	0.05
B	0.8	
bp	0.27	0.37
bq	0.17	0.27
C	0.08	0.150
D	1.15	1.25
E	0.75	0.85
HE	1.15	1.25
Lp	0.15	0.25
θ	0°	7°